16A, 50V - 1000V High Efficient Rectifier

FEATURES

TAIWAN

• AEC-Q101 qualified available

EMICONDUCTOR

- Low forward voltage, high current capability
- Low thermal resistance
- Low power loss, high efficiency
- UL Recognized File # E-326243
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

APPLICATIONS

- DC to DC converter
- Switching mode converters and inverters
- Lighting application
- Snubber
- Freewheeling application

MECHANICAL DATA

- Case: TO-247AD (TO-3P)
- Molding compound meets UL 94V-0 flammability rating
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Meet JESD 201 class 2 whisker test
- Mounting torque: 1.13 N·m maximum
- Polarity: As marked
- Weight: 5.60g (approximately)

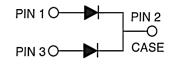
KEY PARAMETERS				
PARAMETER	VALUE	UNIT		
I _F	16	А		
V _{RRM}	50 - 1000	V		
I _{FSM}	200	А		
T _{J MAX}	150	°C		
Package	TO-247AD (TO-3P)			
Configuration	Dual dies			





TO-247AD (TO-3P)

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ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}C$ unless otherwise noted)										
		HER								
PARAMETER	SYMBOL	1601 PT	1602 PT	1603 PT	1604 PT	1605 PT	1606 PT	1607 PT	1608 PT	UNIT
Marking code on the device		HER 1601 PT	HER 1602 PT	HER 1603 PT	HER 1604 PT	HER 1605 PT	HER 1606 PT	HER 1607 PT	HER 1608 PT	
Repetitive peak reverse voltage	V _{RRM}	50	100	200	300	400	600	800	1000	V
Reverse voltage, total rms value	V _{R(RMS)}	35	70	140	210	280	420	560	700	V
Forward current	١ _F	16					А			
Surge peak forward current 8.3ms single half sine wave superimposed on rated load	I _{FSM}	200					A			
Junction temperature	TJ	-55 to +150				°C				
Storage temperature	T _{STG}	-55 to +150				°C				



ELECTRICAL SPECIFICATIONS (1 PARAMETER		CONDITIONS	SYMBOL	ТҮР	MAX	UNIT
HER1601PT		CONDITIONS	STMBOL	116	IVIAA	UNIT
Forward voltage per diode ⁽¹⁾	HER1602PT HER1603PT HER1604PT		V _F	-	1.0	V
	HER1605PT			-	1.3	V
	HER1606PT HER1607PT HER1608PT			-	1.7	V
Reverse current @ rated V _R per diode ⁽²⁾		$T_J = 25^{\circ}C$	-	-	10	μA
		T _J = 125°C	I _R	-	500	μA
Junction capacitance per diode	HER1601PT HER1602PT HER1603PT HER1604PT HER1605PT	1MHz, V _R = 4.0V	CJ	85	-	pF
	HER1606PT HER1607PT HER1608PT			60	-	pF
Reverse recovery time	HER1601PT HER1602PT HER1603PT HER1604PT HER1605PT	I _F = 0.5A, I _R = 1.0A I _{rr} = 0.25A	t _{rr}	-	50	ns
	HER1606PT HER1607PT HER1608PT	I _m = 0.23A		-	80	ns

Notes:

1. Pulse test with PW = 0.3ms

2. Pulse test with PW = 30ms

ORDERING INFORMATION				
ORDERING CODE ⁽¹⁾⁽²⁾	PACKAGE	PACKING		
HER16xPT	TO-247AD (TO-3P)	30 / Tube		
HER16xPTH	TO-247AD (TO-3P)	30 / Tube		

Notes:

1. "x" defines voltage from 50V(HER1601PT) to 1000V(HER1608PT)

2. "H" means AEC-Q101 qualified



CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

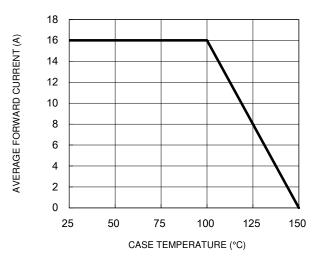


Fig.1 Forward Current Derating Curve

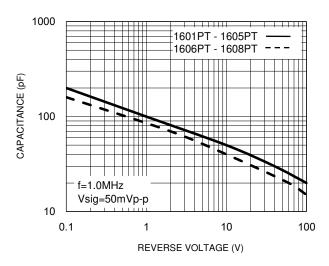
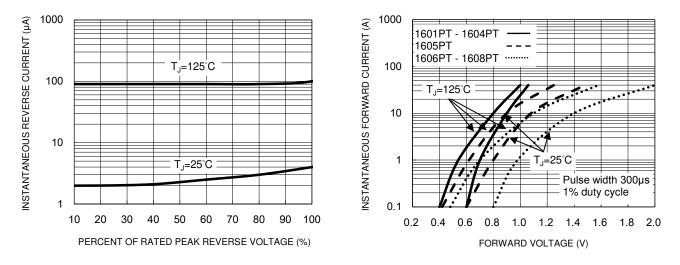


Fig.2 Typical Junction Capacitance

Fig.3 Typical Reverse Characteristics

Fig.4 Typical Forward Characteristics



250 0 0 8.3ms single half sine wave 0 0 0 0 0 0 0 0 0 0 10 10 10 10 NUMBER OF CYCLES AT 60 Hz 3

Fig.5 Maximum Non-Repetitive Forward Surge Current



CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

50Ω 10Ω - trr 🗕 NONINDUCTIVE NONINDUCTIVE w ~~~ +0.5A (-) ± DUT • (+) 50Vdc PULSE 0 GENERATOR (approx) -0.25A (NOTE 2) (-) 1Ω OSCILLOSCOPE 6 (+) (NOTE 1) -1.0A NOTES: 1. Rise Time=7ns max. Input Impedance= ≐ 1 megohm 22pf 2. Rise Time=10ns max. Sourse Impedance= 50 ohms

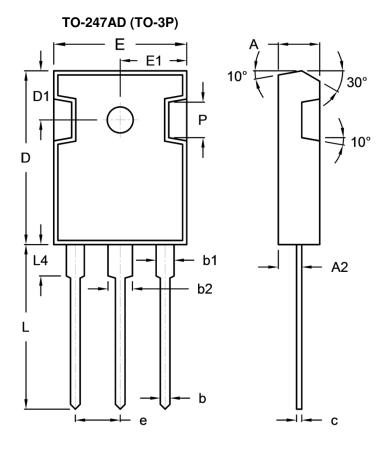
Fig.6 Reverse Recovery Time Characteristic and Test Circuit Diagram



HER1601PT - HER1608PT

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PACKAGE OUTLINE DIMENSIONS



DIM	Unit (m		nm) Unit (
	Min	Max	Min	Max	
А	4.90	5.16	0.193	0.203	
A2	2.70	3.00	0.106	0.118	
b	1.12	1.22	0.044	0.048	
b1	1.93	2.18	0.076	0.086	
b2	2.97	3.22	0.117	0.127	
с	0.51	0.76	0.020	0.030	
D	20.80	21.30	0.819	0.839	
D1	5.70	6.20	0.224	0.244	
E	15.90	16.40	0.626	0.646	
E1	7.90	8.20	0.311	0.323	
е	5.20	5.70	0.205	0.224	
н	2.90	3.40	0.114	0.134	
L	19.70	20.20	0.776	0.795	
L4	3.50	4.10	0.138	0.161	
Р	-	4.30	-	0.169	

MARKING DIAGRAM



= Marking Code
= Green Compound
= Date Code

F = Factory Code



HER1601PT - HER1608PT

Taiwan Semiconductor

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